

REMARKS

The above amendments have been made to correct an obvious editorial mistake in the Amendment filed May 20, 2003. Specifically, lines 7 and 8 from amended claim 1 filed May 20, 2003 were inadvertently duplicated, and this amendment corrects that mistake. For the Examiner's benefit, a marked-up copy of amended independent claim 1 has been submitted herewith.

It is submitted that the arguments presented with the amendment of May 20, 2003 are still applicable to the claims and, thus, the claims are clearly patentable over the prior art of record.

Respectfully submitted,

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

Claim 1 has been amended as follows:

1. (Twice Amended) A method of manufacturing a semiconductor device, comprising:
 - forming a collector layer of a first conductivity type;
 - forming a base region of a second conductivity type formed on a top surface of said collector layer of said first conductivity type, said first conductivity type being opposite said second conductivity type, said base region being formed using epitaxial growth technology, and being formed as a single region having a uniform depth;
 - forming a groove in a top surface of said base region at a portion thereof;
 - forming spacers on sidewalls of said groove;
 - [forming a groove in a top surface of said base region at a portion thereof;
 - forming spacers on sidewalls of said groove;]
 - forming a diffusion source film in said bottom surface of said groove to be embedded therein between said spacers; and
 - forming an emitter region of said first conductivity type in said base region at a bottom surface of said groove, said emitter region being formed in said top surface of said base region at a bottom of said diffusion source film between said spacers.